## Product Summary

| $BV_{DSS}$ (@ $T_J$ Max) | $R_{DS(ON)}$ | $I_D$ $T_C$ = +25°C |
|---|---|---|
| 650V | 2.5Ω@$V_{GS}$ = 10V | 4.5A |

## Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

## Applications

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

## Features

- Low Input Capacitance
- High $BV_{DSS}$ Rating for Power Application
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

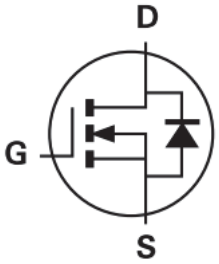
## Mechanical Data

- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram Below
- Weight: TO220AB – 1.85 grams (Approximate)

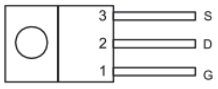
TO220AB

Top View

Bottom View




Equivalent Circuit




Top View
Pin Out Configuration

## Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---|---|---|
| DMG4N60SCT | TO220AB | 50 pieces/tube |

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## Marking Information


= Manufacturer's Marking
4N60SCT = Product Type Marking Code
YYWW = Date Code Marking
YY or $\underline{YY}$ = Last Two Digits of Year (ex: 16 = 2016)
WW or $\underline{WW}$ = Week Code (01 to 53)

## Maximum Ratings (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DSS}$ | 600 | V |
| Gate-Source Voltage | | | $V_{GSS}$ | ±30 | V |
| Continuous Drain Current (Note 5) $V_{GS}$ = 10V | Steady State | $T_C$ = +25°C<br>$T_C$ = +100°C | $I_D$ | 4.5<br>3 | A |
| Maximum Body Diode Forward Current (Note 5) | | | $I_S$ | 6 | A |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%) | | | $I_{DM}$ | 6 | A |
| Avalanche Current, L = 60mH (Note 6) | | | $I_{AS}$ | 1.7 | A |
| Avalanche Energy, L = 60mH (Note 6) | | | $E_{AS}$ | 90 | mJ |

## Thermal Characteristics

| Characteristic | | Symbol | Value | Unit |
|---|---|---|---|---|
| Total Power Dissipation (Note 5) | $T_C$ = +25°C | $P_D$ | 113 | W |
| | $T_C$ = +100°C | | 45 | |
| Thermal Resistance, Junction to Ambient (Note 5) | | $R_{\theta JA}$ | 58 | °C/W |
| Thermal Resistance, Junction to Case (Note 5) | | $R_{\theta JC}$ | 1.1 | |
| Operating and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to +150 | °C |

## Electrical Characteristics (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS (Note 7)** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | 600 | — | — | V | $V_{GS}$ = 0V, $I_D$ = 250µA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | — | — | 1 | µA | $V_{DS}$ = 600V, $V_{GS}$ = 0V |
| Gate-Source Leakage | $I_{GSS}$ | — | — | 100 | nA | $V_{GS}$ = ±30V, $V_{DS}$ = 0V |
| **ON CHARACTERISTICS (Note 7)** | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | 2.5 | — | 4.5 | V | $V_{DS}$ = $V_{GS}$, $I_D$ = 250µA |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 2.0 | 2.5 | Ω | $V_{GS}$ = 10V, $I_D$ = 2A |
| Diode Forward Voltage | $V_{SD}$ | — | — | 1.4 | V | $V_{GS}$ = 0V, $I_S$ = 1A |
| **DYNAMIC CHARACTERISTICS (Note 6)** | | | | | | |
| Input Capacitance | $C_{iss}$ | — | 532 | — | pF | $V_{DS}$ = 25V, f = 1.0MHz, $V_{GS}$ = 0 |
| Output Capacitance | $C_{oss}$ | — | 47 | — | | |
| Reverse Transfer Capacitance | $C_{rss}$ | — | 4 | — | | |
| Gate Resistance | $R_G$ | — | 3.3 | — | Ω | $V_{DS}$ = 0V, $V_{GS}$ = 0V, f = 1.0MHz |
| Total Gate Charge ($V_{GS}$ = 10V) | $Q_g$ | — | 14.3 | — | nC | $V_{DD}$ = 480V, $I_D$ = 4A, $V_{GS}$ = 10V |
| Gate-Source Charge | $Q_{gs}$ | — | 3.3 | — | | |
| Gate-Drain Charge | $Q_{gd}$ | — | 6.9 | — | | |
| Turn-On Delay Time | $t_{D(ON)}$ | — | 14 | — | ns | $V_{DD}$ = 300V, $R_G$ = 25Ω, $I_D$ = 4A, $V_{GS}$ = 10V |
| Turn-On Rise Time | $t_R$ | — | 34 | — | | |
| Turn-Off Delay Time | $t_{D(OFF)}$ | — | 32 | — | | |
| Turn-Off Fall Time | $t_F$ | — | 25 | — | | |
| Body Diode Reverse Recovery Time | $t_{RR}$ | — | 229 | — | ns | dI/dt = 100A/µs, $V_{DS}$ = 100V, $I_F$ = 4A |
| Body Diode Reverse Recovery Charge | $Q_{RR}$ | — | 1564 | — | nC | |

Notes: 5. Device mounted on an infinite heatsink.
6. Guaranteed by design. Not subject to production testing.
7. Short duration pulse test used to minimize self-heating effect.

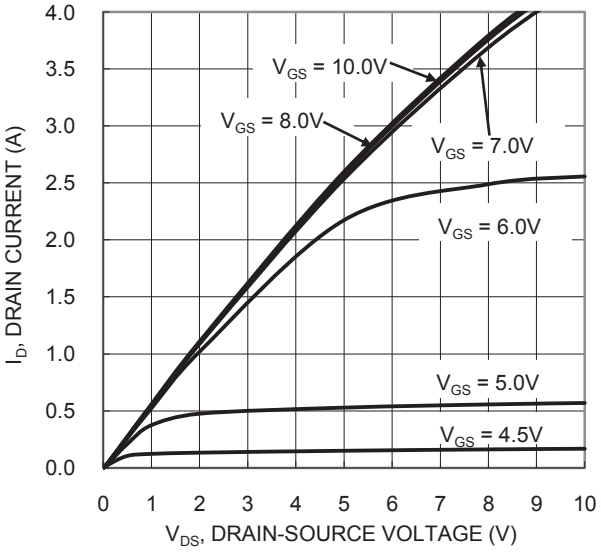



Figure 1. Typical Output Characteristic

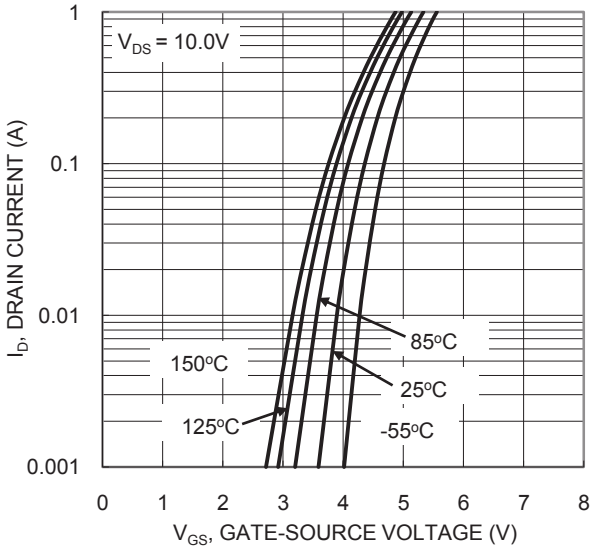



Figure 2. Typical Transfer Characteristic

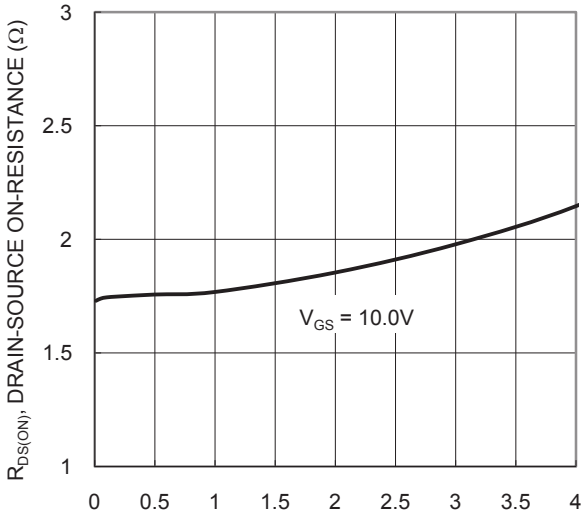



Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

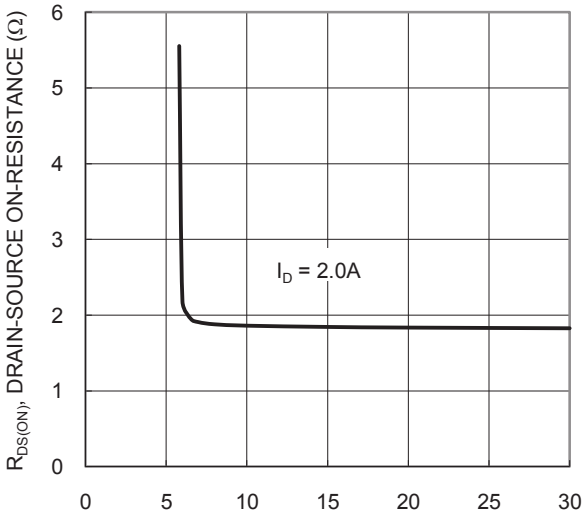



Figure 4. Typical Transfer Characteristic

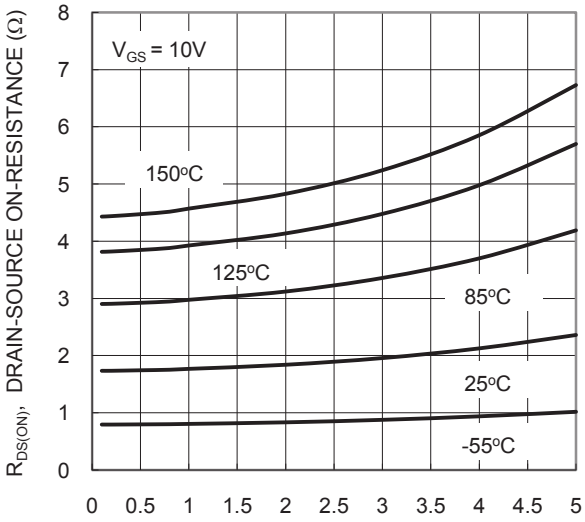



Figure 5. Typical On-Resistance vs Drain Current and Temperature

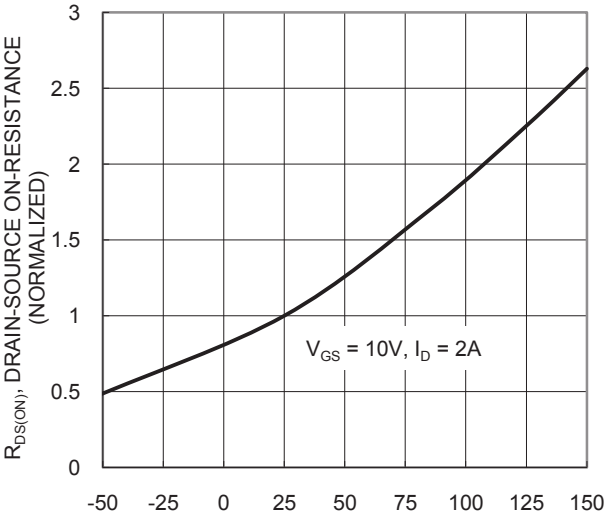



Figure 6. On-Resistance Variation with Temperature

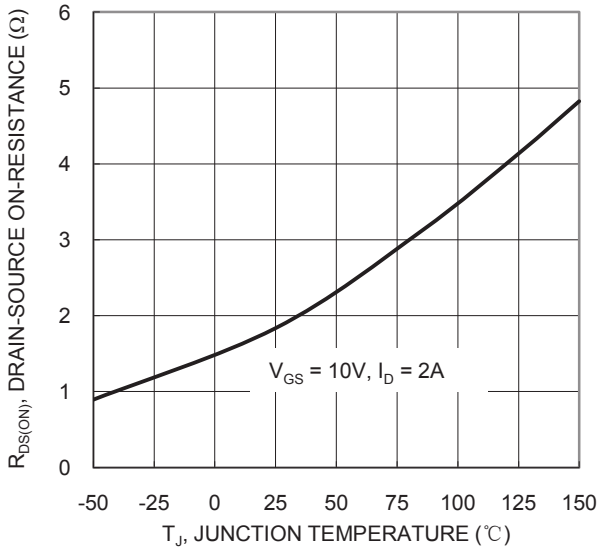



Figure 7. On-Resistance Variation with Temperature

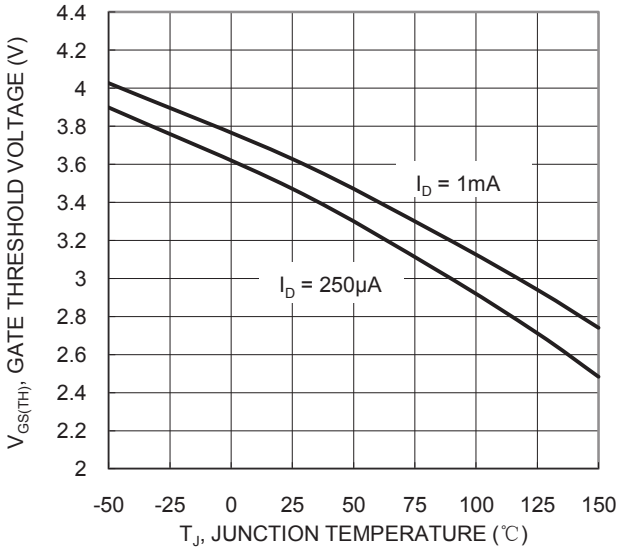



Figure 8. Gate Threshold Variation vs Junction Temperature

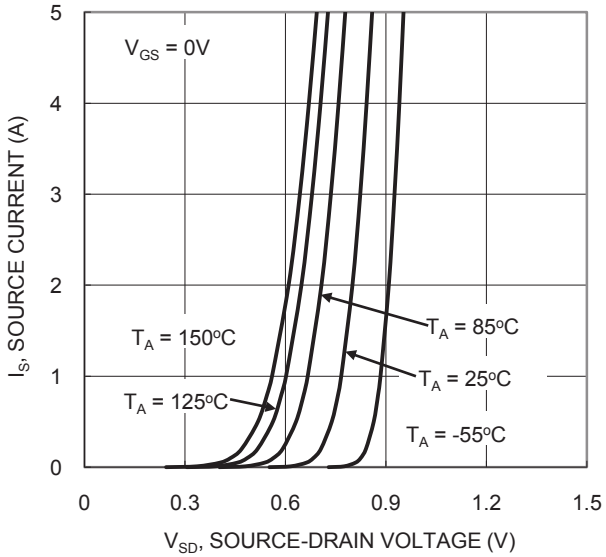



Figure 9. Diode Forward Voltage vs Current

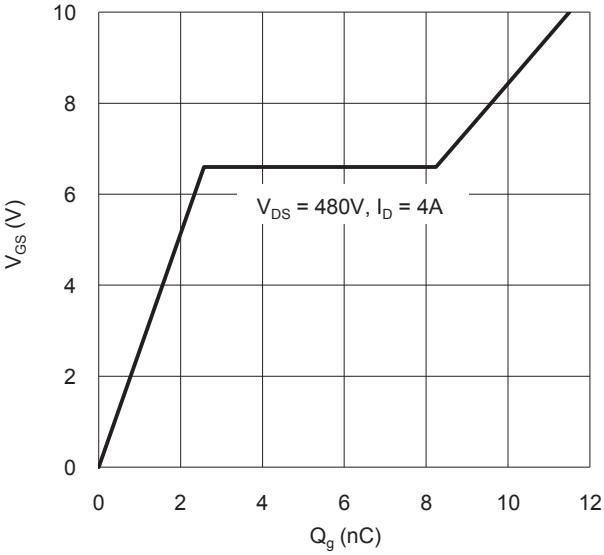



Figure 10. Gate Charge

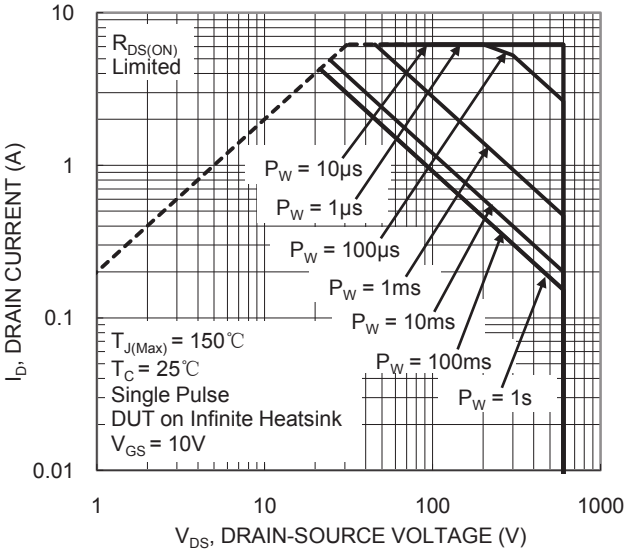



Figure 11. SOA, Safe Operation Area

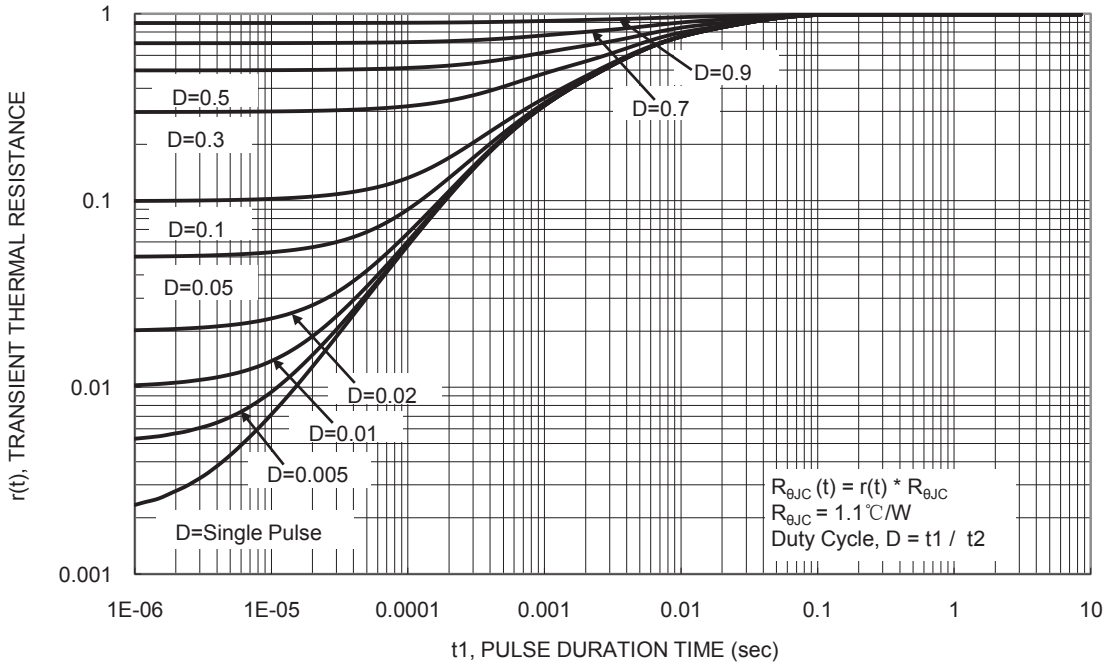
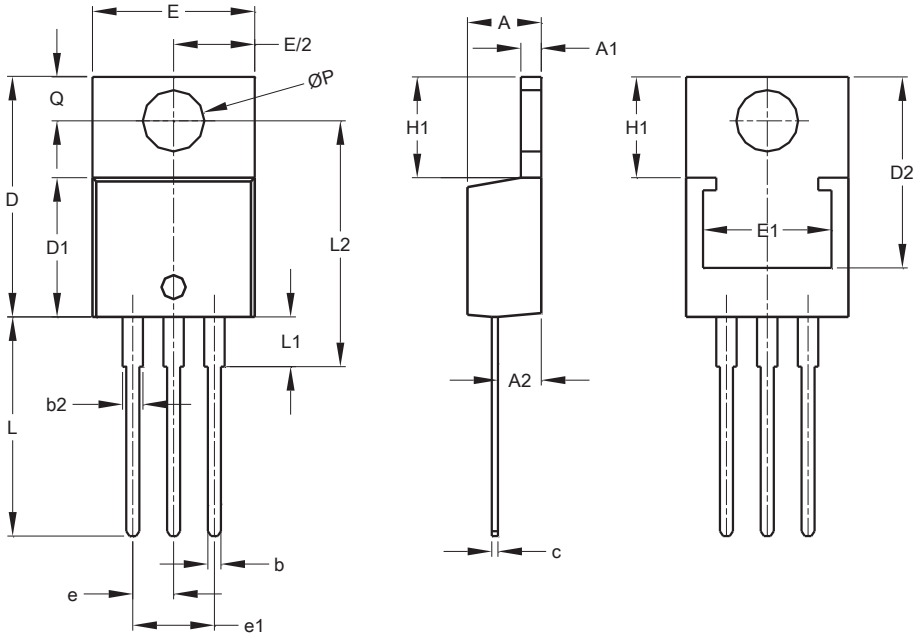



Figure 12. Transient Thermal Resistance

## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

**TO220AB**




| TO220AB | | | |
|---|---|---|---|
| Dim | Min | Max | Typ |
| A | 3.56 | 4.82 | - |
| A1 | 0.51 | 1.39 | - |
| A2 | 2.04 | 2.92 | - |
| b | 0.39 | 1.01 | 0.81 |
| b2 | 1.15 | 1.77 | 1.24 |
| c | 0.356 | 0.61 | - |
| D | 14.22 | 16.51 | - |
| D1 | 8.39 | 9.01 | - |
| D2 | 11.45 | 12.87 | - |
| e | - | - | 2.54 |
| e1 | - | - | 5.08 |
| E | 9.66 | 10.66 | - |
| E1 | 6.86 | 8.89 | - |
| H1 | 5.85 | 6.85 | - |
| L | 12.70 | 14.73 | - |
| L1 | - | 6.35 | - |
| L2 | 15.80 | 16.20 | 16.00 |
| P | 3.54 | 4.08 | - |
| Q | 2.54 | 3.42 | - |
| All Dimensions in mm | | | |

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